

**ABSTRACT OF THE DISCLOSURE**

In a semiconductor device, an interlevel insulating film formed between a Cu interconnection, formed by damascene, and an upper metal interconnection layer on it  
5 has a multilayered structure made up of a Cu diffusion preventive insulating layer and another insulating film. The Cu diffusion preventive insulating layer has a multilayered structure made up of not less than two layers. A method for manufacturing the semiconductor device is  
10 also disclosed.

0903370-064901